

**A TUTORIAL ON
MAJOR HARMONIC BALANCE SOFTWARE**

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Dundas, Ontario, Canada

June 23, 1989

Introduction

we describe the use of Microwave Harmonica - a general purpose linear and nonlinear microwave circuit simulator

we also offer a brief comparison between Libra and Microwave Harmonica

Microwave Harmonica includes Super-Compact which performs linear simulations

nonlinear simulation is performed using harmonic balance method

Microwave Harmonica has a library of linear and nonlinear elements

Microwave Harmonica is capable of performing simulation and optimization of both linear and nonlinear circuits

The Harmonic Balance Method



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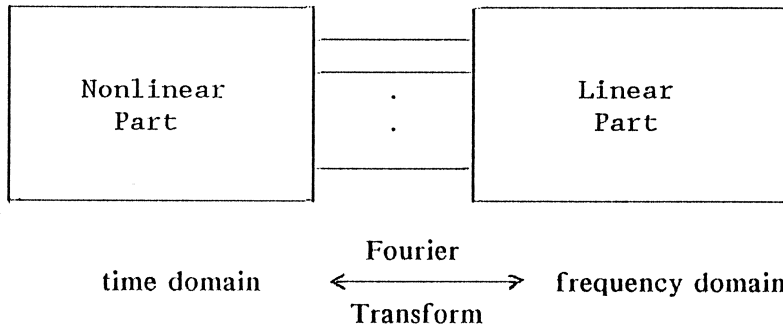
Notation

- $V(k)$ contains external voltages of a linear subcircuit at harmonic k
- $V_t(k)$ contains both internal and external voltages of a linear subcircuit at harmonic k
- $\bar{V}$ contains real and imaginary parts of $V(k)$ for all harmonics
- $\hat{}$ denotes adjoint quantities, e.g., $\hat{V}(k)$
- current vectors $I(k)$, $I_t(k)$, $\bar{I}$ and $\hat{I}(k)$ similarly defined



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Harmonic Balance Simulation



harmonic balance equation

$$\bar{\mathbf{F}}(\bar{\mathbf{V}}) \triangleq \bar{\mathbf{I}}_{\text{NL}}(\bar{\mathbf{V}}) + \bar{\mathbf{I}}_{\text{L}}(\bar{\mathbf{V}}) = \mathbf{0}$$

where $\bar{\mathbf{I}}_{\text{NL}}(\bar{\mathbf{V}})$ and $\bar{\mathbf{I}}_{\text{L}}(\bar{\mathbf{V}})$ represent currents from the linear and the nonlinear parts, respectively

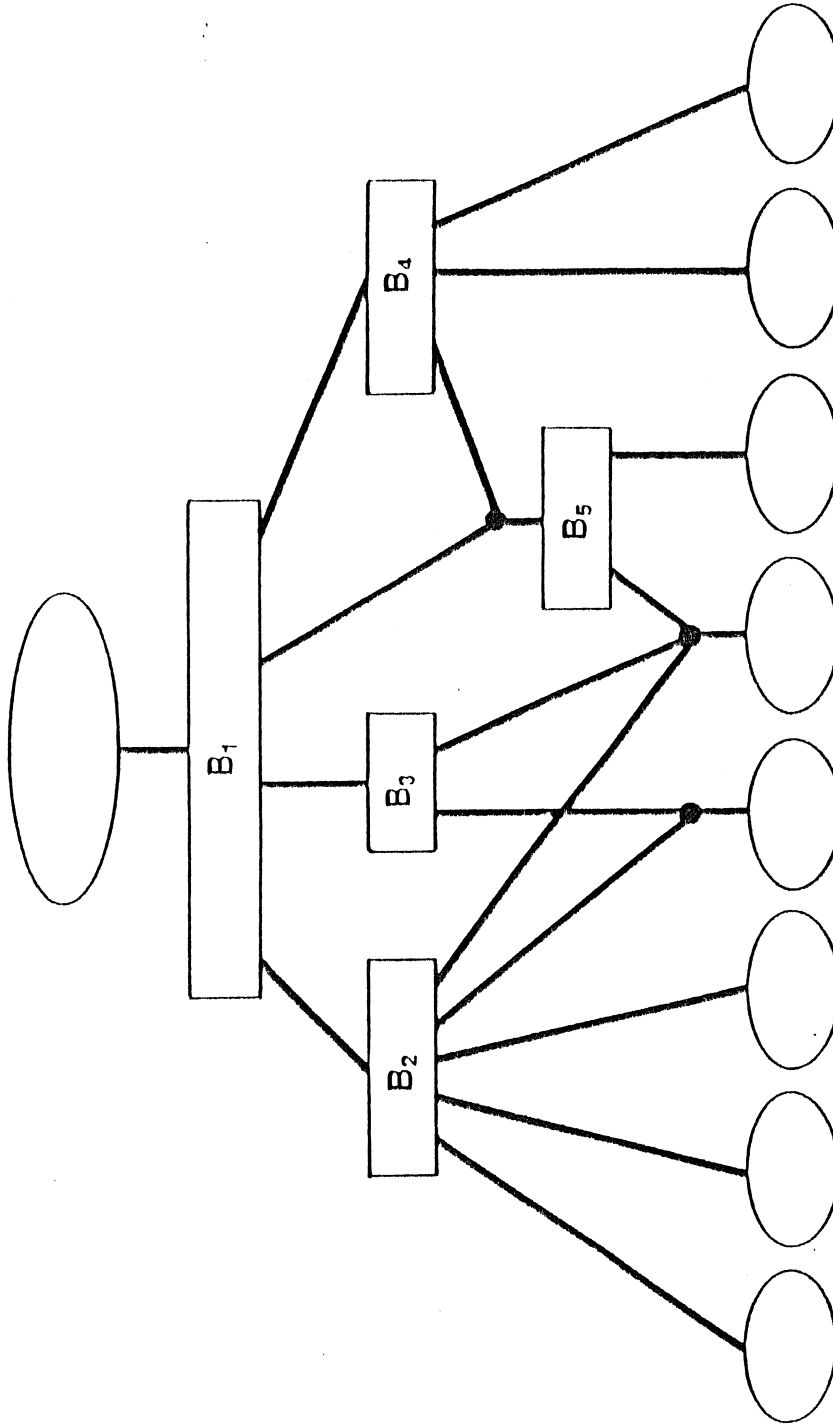
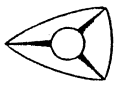
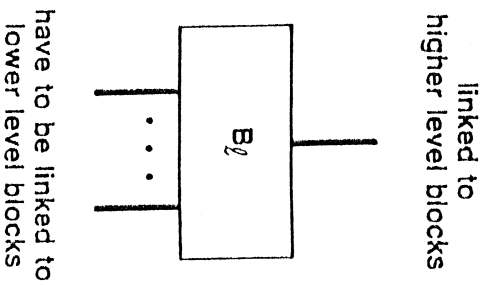


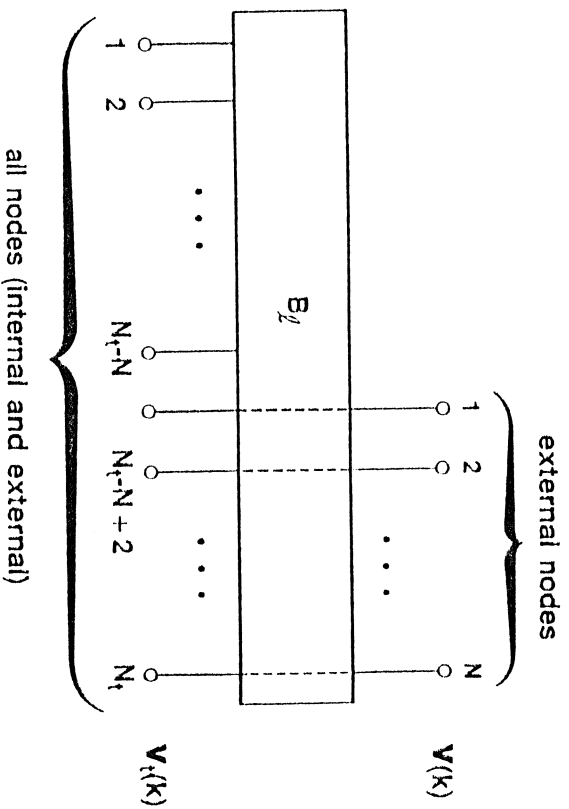
Fig. 1 An arbitrary circuit hierarchy. Each thick line represents a group of nodes. Each rectangular box represents a connection block for a subcircuit. Each bottom circular box represents a circuit element and the top circular box represents the sources and loads.



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(a)



(b)

Fig. 2 A typical subcircuit connection block: (a) as seen from Fig. 1, (b) detailed representation of all the nodes of the subnetwork. Nodes at the top (bottom) of the rectangular box are the external (external and internal) nodes of the subnetwork.



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Hierarchical Analysis

UPWARD analysis is to obtain the overall circuit matrix, e.g., Y matrix, for the linear part

DOWNWARD analysis is to obtain responses for the linear part at individual components, e.g., voltage or power for an element

TOP LEVEL analysis is to solve the harmonic balance equations for nonlinear networks

TOP LEVEL analysis is to solve the terminated circuit for linear networks



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Top Level Simulation of Nonlinear Circuits

harmonic balance equation

$$\overline{\mathbf{F}}(\overline{\mathbf{V}}) = \mathbf{0}$$

Newton update

$$\overline{\mathbf{V}}_{\text{new}} = \overline{\mathbf{V}}_{\text{old}} - \overline{\mathbf{J}}^{-1} \overline{\mathbf{F}}(\overline{\mathbf{V}}_{\text{old}})$$

$\overline{\mathbf{J}}$ is the Jacobian matrix

the Newton solution provides the top level voltages $\mathbf{V}(\mathbf{k})$



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Downward Simulation of the Original Linear Network

consider a typical subcircuit

internal and external voltages $V_t(k)$ of the subcircuit can be computed from its external voltages $V(k)$ by

$$A(k) \begin{bmatrix} V_t(k) \\ I(k) \end{bmatrix} = \begin{bmatrix} 0 \\ V(k) \end{bmatrix}$$

$A(k)$ is the modified nodal admittance matrix of the subcircuit

$I(k)$ contains currents into the subcircuit from its external ports

$V_t(k)$, along with $I(k)$, is a solution to the subcircuit

Implementation

suppose subcircuits C1, C2 and C3 are directly connected to the subcircuit under consideration from below

then solution $V_t(k)$ contains internal and external voltages of the subcircuit under consideration

$V_t(k)$ also provides external voltages of the lower level subcircuits C1, C2, C3

the equation is used iteratively down the hierarchy until all desired voltages are found

Input File Syntax

circuit blocks

harmonic indices for excitation and outputs

single tone case

two tone case

frequency sweep and power sweep syntax

NVAR block

DC state variables: fix or optimize

AC state variables: fix or optimize

Nonlinear Device Models

device model covers the intrinsic part of the nonlinear models

users can describe FET parasitic or packaging effects using linear elements

user can define nonlinear device models through a subroutine

Linear Elements

the concept of primary and secondary elements

primary elements - can be used to create subcircuits

secondary elements - can be optimized

user can define linear elements through a subroutine

Control Options for HB Simulation

harmonic balance simulation is iterative

factors affecting convergence

- device operating in highly nonlinear regions
- excitation level very high
- insufficient number of harmonics considered
- accuracy specified is too small

convergence for diode circuits are usually slow - it is recommended not to use default control options

State Variable File

state variable solutions are automatically stored in the file
***.VAR**

management of the *.var file

keep the file name consistent with that of the circuit file

users are not encouraged to alter this file

Exploiting Sparse Simulator

subcircuits defined by primary circuits can be solved efficiently by the built-in sparse solver

DC Simulation

Microwave Harmonica requires that AC excitation should not be DC connected to bias ports

Frequency Sweep

small frequency step in frequency sweep will improve convergence

Microwave Harmonica Handles Frequency Degeneracy

if a frequency degeneracy occurs in a two tone case then one of the two exciting frequencies will be slightly perturbed

Libra and Microwave Harmonica - A Brief Comparison

The comparison is mainly focused on the harmonic balance features of the two products

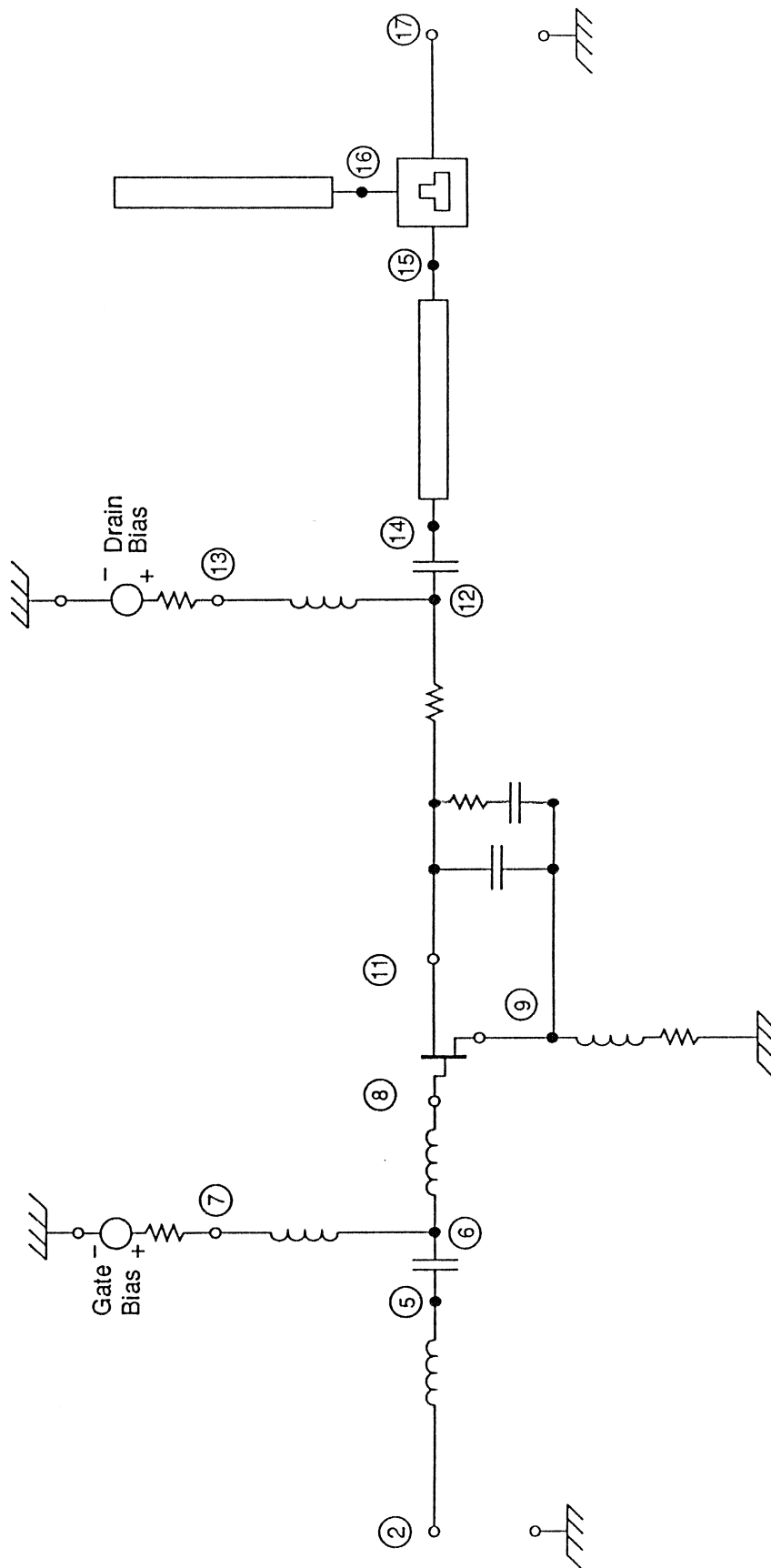


Fig. 2 Augmented linear subnetwork for the frequency doubler depicted in Fig. 1.

EXAMPLE 1

CIRCUIT FILE FOR MICROWAVE HARMONICA

* EXAMPLE 1: STARTING OPTIMIZATION OF A FET FREQUENCY DOUBLER

NBLK

```

      SUBS EPSR=9.8          ! *** DEFAULTS: H=.635E-3 SIGD=0 T=6E-6 ROC=3.85E-8 RHS=.15E-6
      SRLC 6 8 L=.16NH
      CAP1: PRLC 5 6 C=20PF  ! *** SUCH A LABEL NOT AVAILABLE IN LIBRA
      IND1: SRLC 6 7 L=15NH  ! *** SUCH A LABEL NOT AVAILABLE IN LIBRA
*
      SRLC 11 9 R=440 C=1.15PF
      PRLC 11 9 C=.12PF
      SRLC 11 12 R=2.153
      SRLC 9 0 R=1.144 L=0.07NH
      CAP1 12 14
      IND1 12 13
*
      SRLC 2 5 L=? .5NH 1NH 10NH? Q=50 ! *** FREQUENCY INDEPENDENT QUALITY FACTOR Q
      MIC 14 15 0 0 P=? .5E-3 1.E-3 10.E-3? W=.1E-3
      MICO 16 0 P=? 1.E-3 5.E-3 10.E-3? W=.635E-3
      TJUN 16 15 17 0 0 0 W1=.635E-3 W2=.1E-3 W3=.635E-3 X=1 ! *** X - DISPLACEMENT PARAMETER
*
      NFET 8 11 9 ! *** MATERKA & KACPRZAK MODEL NOT AVAILABLE IN LIBRA
+ IDSS=6.E-2 VP0=-1.906 GAMA=-1.5E-2 E=1.8
+ SL=.676E-1 KG=1.1 T=7.E-12 SS=1.666E-3
+ IGO=.713E-5 AFAG=38.46 R10=3.5 KR=1.111
+ IB0=-.713E-5 AFAB=-38.46 C10=0.42E-12 K1=1.282
+ CF0=0.02E-12 KF=1.282 VBC=0. VDMX=10.0 NAME=MY_FET
*
      BIAS 7 0 V=FREE R=100 NAME=GT_BIAS ! *** ONLY IDEAL DC SOURCES AVAILABLE IN LIBRA
      BIAS 13 0 V=FREE R=100 NAME=DR_BIAS ! *** ONLY IDEAL DC SOURCES AVAILABLE IN LIBRA
*
      DOUBLER: 2PORT 2 0 17 0
END
FREQ
      HARM 4
      5GHZ
END
NEXC
      P1<H1>=2.E-3WATT ! *** ONLY FUNDAMENTAL FREQUENCY SOURCES AVAILABLE IN LIBRA
END
NOPT
      TG21<H2,H1>=2.5DB GT W=.005
      + SP2<H2> = 19DB GT W=.005
END
NVAR
      MY_FET VGS<H0>=-1.906 VGS<H1>=? .001 0? ! *** STATE VARIABLES NOT INITIALIZED IN LIBRA
      + VDS<H0>=5. VDS<H1>=? .001 0?
END

```

EXAMPLE 1

CIRCUIT FILE TRANSLATED TO THE LIBRA FORMAT

```

! EXAMPLE 1: STARTING OPTIMIZATION OF A FET FREQUENCY DOUBLER
! LIBRA FORMAT
DIM
  PWR W          ! default dBm
  CUR A          ! default mA
  VOL V          ! EQUALS DEFAULT (can be omitted)
  FREQ GHZ       ! EQUALS DEFAULT (can be omitted)
  RES OH         ! EQUALS DEFAULT (can be omitted)
  IND NH         ! EQUALS DEFAULT (can be omitted)
  CAP PF         ! EQUALS DEFAULT (can be omitted)
  LNG MM        ! default MIL (meters not available)
VAR             ! similar to MICROWAVE HARMONICA labels
  CAP1 = 20.0
  IND1 = 15.0
CKT
  MSUB ER=9.8 H=.635 T=6E-3 RHO=1.58 RGH=.15E-3      ! all parameters must be specified in the
                                                    ! prescribed order; 1.58 = 3.85/2.44

  IND 6 8 L=.16
  CAP 5 6 C^CAP1
  IND 6 7 L^IND1
! RES 11 12 R=2.153      ! NOT NEEDED (included in the FET model)
! SRC 11 9 R=440 C=1.15  ! NOT NEEDED (included in the FET model)
! CAP 11 9 C=0.12        ! NOT NEEDED (included in the FET model)
! RES 9 10 R=1.144      ! NOT NEEDED (included in the FET model)
  IND 10 0 L=0.07
  CAP 12 14 C^CAP1
  IND 12 13 L^IND1
  INDQ 2 5 L # 0.5 1.0 10.0 Q=50 F=1 MOD=3          ! frequency independent quality factor Q
  MLIN 14 15 W=.1 L # 0.5 1.0 10.0
  MLOC 16 W=.635 L # 1.0 5.0 10.0
  MTEE 16 15 17 W1=.635 W2=.1 W3=.635              ! compare layout in LIBRA and MICROWAVE HARMONICA;
                                                    ! displacement parameter not available in LIBRA

! -----
! Note: LIBRA does not support the Materka & Kacprzak model. To solve this problem we may convert the Materka
! & Kacprzak model to Curtice model and use it in the Libra circuit file and, if the models do not match
! well, use the Curtice model in the MICROWAVE HARMONICA circuit file as well. HarPE can be used to
! convert one model to the other. The parameters in the MODEL block in this circuit file may not match
! the device described in the MICROWAVE HARMONICA circuit file.

  S2PA_A1 8 12 10 [MODEL=MY_FET]
! -----
* VS_G_BIAS 107 0 DC \ -1.906      ! only ideal DC sources are supported in LIBRA; optimization unclear
  RES 107 7 R=100                  ! must be separated from the source
* VS_D_BIAS 113 0 DC \ 5          ! only ideal DC sources are supported in LIBRA; optimization unclear
  RES 113 13 R=100                 ! must be separated from the source
* RES_RG 1 2 R=50
* RES_RL 17 0 R=50
  DEF2P 2 17 DOUBLER
SOURCE
  DOUBLER P_INP_P 1 0 R=RES_RG P^PWR F^F1
MODEL
  MY_FET GAS MODEL=2 RS=1.144 RD=2.153 RG=0 RC=440 CRF=1.15P &
    A0=0.065 A1=0.115 A2=0.059 A3=0.009 &
    GAMMA=2 BETA=0.04 VDS0=2.0 VSDSC=2.0 RDS0=1250 &
    IS=1.E-9 N=1.5 CGD0=0.06P CGS0=0.37P CDS=0.12P
FREQ
  STEP 5
  NH = 4
POWER
  STEP 2.E-3
FILEOUT
  DOUBLER HB STATE EXAMPLE1.HBV      ! automatically done in MICROWAVE HARMONICA
OUT
  DOUBLER PS_OUT_P 17 0 R=RES_RL GR1 ! interactively accessed in MICROWAVE HARMONICA
GRID
  RANGE 0 25 2.5                    ! interactively accessed in MICROWAVE HARMONICA
  GR1 -80 20 10
HBCNTL
  RELTOL = 1E-6                      ! interactively accessed in MICROWAVE HARMONICA
  SAMPLE = 3.0
OPT ! not clear what and how can be optimized; nonlinear optimization is announced for Libra 2.1

```

BRIEF COMPARISON OF LIBRA AND MICROWAVE HARMONICA

The comparison is mainly focused on the harmonic balance features. Libra V1.0 Users Manual (December, 1987) is used as the basis for evaluating Libra.

Microwave Harmonica is referred to as MH.

1. Optimization of Nonlinear Circuits

Libra: recently claimed for Libra 2.1 (in Microwave Journal May 1989)
MH: yes

2. Nonlinear Circuit Responses

Libra: power spectrum, waveform and spectrum of voltages and currents
MH: power spectrum, waveform and spectrum of voltages and currents

Libra: spectral density
MH: spectral purity, return loss, power added efficiency, transducer gain, transfer efficiency

3. Operating Frequencies of AC Sources

Libra: only at fundamental frequencies F1 and F2 (see p. 2-34)
MH: at fundamental, higher harmonics or intermodulating frequencies

4. Treatment of Mixer Case

Libra: spectrum defined by various intermodulating harmonics of the LO and RF frequencies
MH: spectrum efficiently defined by number of LO harmonics and number of side bands per LO harmonic

5. Unified Element Representation for Linear and Nonlinear Analysis

Libra: the syntax for linear and nonlinear elements is different; a star * must appear in front of elements relevant for harmonic balance; the names of such elements are mostly a mixture of internal keywords and user-specified character strings
MH: the syntax for linear and nonlinear elements is the same

6. Style of Outputs for Linear and Nonlinear Analysis

Libra: for linear outputs, user specifies response keyword and port number;
for nonlinear outputs, user specifies response keyword, node number and harmonic numbers
MH: for linear outputs, user specifies response keyword and port number;
for nonlinear outputs, user specifies response keyword, port number and harmonic numbers; also, interactive selection of the desired output is available

7. User's Access to State Variables

Libra: no access

MH: yes (user can specify bounds or fix some state variables)

8. User-Defined Nonlinear Elements

Libra: not clear

MH: yes (user can define his or her elements in a subroutine)

9. Built-in Models

Libra: diode; FET: Curtice model, Raytheon model, EEsof model; BJT

MH: diode; FET: Materka model, Curtice model; BJT

The following compares features similar in Libra and MH

10. Nonlinear Elements in Circuit Hierarchy

Libra: only at the highest hierarchy

MH: only at the highest hierarchy

11. Substrate Parameters Defined by a Special Element in Circuit Block

Libra: yes (the special element are MSUB, SSUB, SSSUB)

MH: yes (the special element is SUBS)

12. Ungrounded External Ports at the Top Circuit Hierarchy

Libra: allowed

MH: allowed

13. DC Sources

Libra: DC sources can be defined in either the circuit block or the source blocks (in CKT block or SOURCE block)

MH: DC sources can be defined in either the circuit block or the excitation block (in NBLK block or NEXC block)

14. AC Sources

Libra: AC sources can be defined in either the circuit block or the source block, but it is recommended to defined them in source block.

MH: AC sources are defined in the excitation block (NEXC block)

15. Saving and Reusing State Variable Solutions

Libra: yes (file .HBV)

MH: yes (file .VAR)

16. Harmonic Balance Control Variables (accuracy, number of iterations, etc.)

Libra: defined in circuit file

MH: accessed interactively; more parameters can be controlled

17. FET Parasitics

Libra: topology fixed internally; parameters are defined within FET model

MH: arbitrarily defined by the user as ordinary linear elements

```

! Example testm.ckt
! Optimization to fit S-parameter and DC bias measurement data.
! Model used: Built-in Materka and Kacprzak model.
!
Expression
  GDS_MODEL = 1./440.
END
Model

  Extrinsic2      1 2 3 4 5
    LG:      0.16NH
    RG:       0
    RD:      2.153
    LD:       0
    RS:      1.144
    LS:      0.07NH
    GDS:      GDS_MODEL
    CX:      1.15PF
    CDS:      0.12PF ;

  FETM      1 2 3
    IDSS:      6.e-2
    VP0:      -1.906
    E:         1.8
    ! KE:       0
    SL:        .676E-1
    KG:         1.1
    SS:        1.666E-3
    IG0:        .713E-5
    ALPHAG:     38.46
    IB0:       -0.713E-5
    ALPHAB:    -38.46
    R10:        3.5
    KR:         1.111
    K1:         1.282
    ! C1S:      0.0048PF
    CF0:       0.02PF
    KF:        1.282 ;

    ! Materka FET model
    GAMMA:    -1.5E-2
    TAU:      7PS
    VBC:      0
    C10:      0.42PF

  2POR 4 5;
end

Data
! S-parameter measurement data

#include "spar_1.dat"
end

Sweep
! HB simulation

! FREQ: 0.2GHZ 6GHZ 10GHZ PIN: 5DBM VG: -0.673 VD: 4;
! FREQ: 6GHZ PIN: from -15DBM to 10DBM step=5DBM VG: -0.673 VD: 4;

! S-parameter simulation

```

FREQ: from 2GHZ to 20GHZ STEP=2GHZ VG: 0 -1 -2 VD: 2 4;

! DC IV simulation

VG: 0.5 0 -0.5 -1 -1.5 -2 VD: FROM 0 TO 4 STEP=0.25;
end

Specification

FREQ: from 2GHZ to 18GHZ step=3GHZ MS11 PS11 MS21 PS21 MS12 PS12 MS22 PS22;
VG: 0 -1.74 -3.1 VD: 4 ID 50; ! weighting factor for ID is 50
end

```

! Example testc.ckt
! optimization to fit S-parameter and DC data.
! Model used: Built-in Curtice and Ettenberg cubic model.
!

```

Expression

```

GDS_MODEL = 1./440.
END

```

Model

```

Extrinsic2      1 2 3 4 5
      LG:      0.16NH
      RG:       0
      RD:      2.153
      LD:       0
      RS:      1.144
      LS:      0.07NH
      GDS:     GDS_MODEL
      CX:      1.15PF
      CDS:     0.12PF ;

```

```

FETC  1 2 3      ! Curtice FET model
      A0:   ?0  0.0644434  0.3?      A1:   ?0.0544248 ?
      A2:   ? -0.00359251 ?          A3:   ? -0.00928337 ?
      GAMMA: ? 1.00546 ?              BETA: ?-2  0.0529885  2?
      VDS0:   3
      IS:     ? 3.53605e-06 ?          N:     ? 1.18411 ?
      CGS0:   ? 0.380929PF ?          CGD0: ? 0.0184392PF ?
      FC :    ? 0.760981 ?            GMIN: ? 1.25927e-07 ?
      VBI:    ? 1.20067 ?            VBR:   10.0;

```

```

      2POR  4  5;
end

```

Data

```

! simulated DC IV data

```

```

#include "test_s1.dat"
#include "test_s2.dat"
#include "test_s3.dat"
#include "test_s4.dat"
#include "test_s5.dat"
#include "test_s6.dat"

```

```

#include "test_dc.dat"
end

```

Sweep

```

! S-parameter simulation

```

```

FREQ: from 2GHZ to 20GHZ STEP=2GHZ  VG: 0 -1 -2      VD: 2  4;

```

! DC IV simulation

VG: 0.5 0 -0.5 -1 -1.5 -2 VD: FROM 0 TO 4 STEP=0.25;

end

Specification

FREQ: from 2GHZ to 20GHZ step=3GHZ MS11 PS11 MS21 PS21 MS12 PS12 MS22 PS22;

VG: 0.5 0 -1 -2 VD: 0.5 2 4 ID 20;
end

```

! Example testr.ckt
! optimization to fit S-parameter and DC data.
! Model used: Built-in Raytheon (Statz et al.) model.
!

```

Expression

```

GDS_MODEL = 1./440.
END

```

Model

```

Extrinsic2      1 2 3 4 5
                LG:   0.16NH
                RG:    0
                RD:   2.153
                LD:    0
                RS:   1.144
                LS:   0.07NH
                GDS:  GDS_MODEL
                CX:   1.15PF
                CDS:  0.12PF ;

```

```

FETR      1 2 3
          ALPHA =? 1.2031 ?
          VTO = ? -1.99521 ?
          LAMBDA = ? 0.0391735 ?
          TAU:  7PS
          IS:   ? 3.18301e-06 ?
          CGS0: ? 0.389679PF ?
          FC :  ? 0.723868 ?
          VBI:  ? 1.19925 ?

```

```

BETA = ? 0.0136191 ?
THETA = ? 0.000240122 ?

N:      ? 1.31133 ?
CGD0: ? 0.0203977PF ?
GMIN: ? 1.27192e-07 ?
VBR:  10.0;

```

```

2POR 4 5;
end

```

Data

```

! simulated DC IV data

```

```

#include "test_s1.dat"
#include "test_s2.dat"
#include "test_s3.dat"
#include "test_s4.dat"
#include "test_s5.dat"
#include "test_s6.dat"

```

```

#include "test_dc.dat"
end

```

Sweep

```

! S-parameter simulation

```

```

FREQ: from 2GHZ to 20GHZ STEP=2GHZ  VG: 0 -1 -2      VD: 2 4;

```

! DC IV simulation

VG: 0.5 0 -0.5 -1 -1.5 -2 VD: FROM 0 TO 4 STEP=0.25;

end

Specification

FREQ: from 2GHZ to 20GHZ step=3GHZ MS11 PS11 MS21 PS21 MS12 PS12 MS22 PS22;

VG: 0.5 0 -1 -2 VD: 0.5 2 4 ID 20;
end

file: tutorial.dat

Data for Materka model

! DC Data (I-V Characteristics)

!

PARAMETER VG=0.5V;

FORMAT VD(V) ID(mA);

0.0000	-113.5730
0.2500	-13.7797
0.5000	33.5464
0.7500	49.3960
1.0000	60.6714
1.2500	67.8620
1.5000	72.0954
1.7500	74.5267
2.0000	75.9763
2.2500	76.9250
2.5000	77.6272
2.7500	78.2101
3.0000	78.7354
3.2500	79.2328
3.5000	79.7172
3.7500	80.1951
4.0000	80.6694

PARAMETER VG=0V;

FORMAT VD(V) ID(mA);

0.0000	-0.0063
0.2500	13.3452
0.5000	25.1776
0.7500	34.9614
1.0000	42.5600
1.2500	48.1533
1.5000	52.1063
1.7500	54.8335
2.0000	56.7065
2.2500	58.0144
2.5000	58.9612
2.7500	59.6825
3.0000	60.2654
3.2500	60.7641
3.5000	61.2121
3.7500	61.6291
4.0000	62.0276

PARAMETER VG=-0.5V;

FORMAT VD(V) ID(mA);

0.0000	0.0002
0.2500	5.7430
0.5000	11.1542
0.7500	16.0296
1.0000	20.2521
1.2500	23.7882
1.5000	26.6704

1.7500	28.9730
2.0000	30.7892
2.2500	32.2145
2.5000	33.3356
2.7500	34.2255
3.0000	34.9432
3.2500	35.5345
3.5000	36.0337
3.7500	36.4668
4.0000	36.8520

PARAMETER VG=-1V;

FORMAT VD(V) ID(mA);

0.0000	0.0001
0.2500	2.0512
0.5000	4.0552
0.7500	5.9550
1.0000	7.7077
1.2500	9.2865
1.5000	10.6806
1.7500	11.8922
2.0000	12.9328
2.2500	13.8196
2.5000	14.5726
2.7500	15.2122
3.0000	15.7572
3.2500	16.2250
3.5000	16.6304
3.7500	16.9858
4.0000	17.3017

PARAMETER VG=-1.5V;

FORMAT VD(V) ID(mA);

0.0000	-0.0000
0.2500	0.3979
0.5000	0.8007
0.7500	1.2003
1.0000	1.5889
1.2500	1.9605
1.5000	2.3108
1.7500	2.6367
2.0000	2.9372
2.2500	3.2125
2.5000	3.4631
2.7500	3.6913
3.0000	3.8989
3.2500	4.0885
3.5000	4.2617
3.7500	4.4214
4.0000	4.5692

PARAMETER VG=-2V;

FORMAT VD(V) ID(mA);

0.0000	-0.0000
--------	---------

0.2500	-0.0000
0.5000	0.0000
0.7500	0.0000
1.0000	0.0000
1.2500	0.0000
1.5000	0.0000
1.7500	0.0000
2.0000	0.0000
2.2500	0.0001
2.5000	0.0000
2.7500	0.0001
3.0000	0.0000
3.2500	0.0001
3.5000	0.0001
3.7500	0.0001
4.0000	0.0000

! Small-Signal S-Parameters

!

PARAMETER VG=0V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9900	-15.00	4.1207	165.26	0.0063	87.51	0.4291	-9.27
3.00	0.9369	-43.64	3.7996	140.53	0.0180	85.00	0.4187	-17.12
5.00	0.8638	-69.20	3.3642	118.13	0.0281	85.32	0.4178	-26.06
7.00	0.7994	-91.45	2.9327	98.71	0.0377	88.17	0.4225	-34.62
9.00	0.7545	-110.91	2.5593	81.73	0.0485	92.03	0.4327	-42.86
11.00	0.7296	-128.15	2.2492	66.54	0.0616	95.43	0.4480	-50.91
13.00	0.7217	-143.62	1.9912	52.65	0.0776	97.59	0.4674	-58.84
15.00	0.7271	-157.66	1.7716	39.70	0.0966	98.31	0.4898	-66.71

! Small-Signal S-Parameters

!

PARAMETER VG=-0.5V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9942	-12.13	3.0760	166.81	0.0056	88.49	0.4162	-9.16
3.00	0.9533	-35.74	2.9100	144.62	0.0162	87.34	0.4081	-16.67
5.00	0.8897	-57.76	2.6716	123.59	0.0258	88.15	0.4096	-25.62
7.00	0.8243	-77.96	2.4088	104.59	0.0350	91.02	0.4154	-34.34
9.00	0.7696	-96.51	2.1591	87.52	0.0454	94.85	0.4259	-42.74
11.00	0.7307	-113.72	1.9354	72.04	0.0580	98.32	0.4407	-50.91
13.00	0.7078	-129.79	1.7381	57.82	0.0736	100.57	0.4593	-58.91
15.00	0.6993	-144.86	1.5621	44.56	0.0923	101.32	0.4808	-66.80

! Small-Signal S-Parameters

!

PARAMETER VG=-1V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9956	-10.41	2.1191	167.44	0.0052	87.54	0.5525	-8.63
3.00	0.9632	-30.88	2.0326	146.68	0.0148	84.97	0.5412	-15.76
5.00	0.9092	-50.50	1.9080	126.39	0.0226	85.08	0.5397	-24.34
7.00	0.8480	-69.10	1.7596	107.55	0.0292	89.02	0.5415	-32.75
9.00	0.7908	-86.77	1.6067	90.26	0.0366	95.90	0.5474	-40.89
11.00	0.7439	-103.71	1.4590	74.39	0.0470	103.04	0.5576	-48.83
13.00	0.7100	-120.04	1.3196	59.74	0.0618	107.96	0.5715	-56.65
15.00	0.6895	-135.78	1.1879	46.12	0.0809	109.98	0.5881	-64.42

! Small-Signal S-Parameters

!

PARAMETER VG=-1.5V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9966	-9.21	1.0998	167.65	0.0050	86.19	0.7272	-8.37
3.00	0.9713	-27.48	1.0663	147.72	0.0139	81.36	0.7125	-15.29
5.00	0.9266	-45.39	1.0198	127.83	0.0202	79.51	0.7090	-23.76
7.00	0.8715	-62.85	0.9594	109.05	0.0239	83.64	0.7075	-32.21
9.00	0.8145	-79.92	0.8903	91.63	0.0277	95.19	0.7085	-40.46
11.00	0.7621	-96.71	0.8162	75.63	0.0358	109.33	0.7124	-48.53
13.00	0.7184	-113.28	0.7392	61.02	0.0506	118.45	0.7189	-56.48
15.00	0.6855	-129.61	0.6604	47.76	0.0716	121.31	0.7271	-64.33

! Small-Signal S-Parameters

!

PARAMETER VG=-2V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9976	-8.31	0.0048	85.68	0.0048	85.68	0.8138	-8.29
3.00	0.9785	-24.92	0.0133	79.94	0.0133	79.94	0.7993	-15.07
5.00	0.9427	-41.55	0.0189	76.82	0.0189	76.82	0.7981	-23.62
7.00	0.8944	-58.22	0.0213	80.22	0.0213	80.22	0.7977	-32.35
9.00	0.8388	-74.96	0.0230	94.55	0.0230	94.55	0.7975	-41.05
11.00	0.7813	-91.80	0.0300	114.44	0.0300	114.44	0.7971	-49.61
13.00	0.7272	-108.72	0.0457	125.84	0.0457	125.85	0.7964	-58.01
15.00	0.6804	-125.61	0.0682	128.10	0.0682	128.10	0.7950	-66.18

Data for Curtice model

! DC Data (I-V Characteristics)

!

PARAMETER VG=0.5V;

FORMAT VD(V) ID(mA);

0.0000	-88.7760
0.2500	-3.4374
0.5000	22.3196
0.7500	37.7115
1.0000	50.5700
1.2500	60.5621
1.5000	67.8117
1.7500	72.7602
2.0000	75.9659
2.2500	77.9477
2.5000	79.1153
2.7500	79.7602
3.0000	80.0773
3.2500	80.1918
3.5000	80.1823
3.7500	80.0972
4.0000	79.9660

PARAMETER VG=0V;

FORMAT VD(V) ID(mA);

0.0000	0.0000
0.2500	13.0354
0.5000	24.8927
0.7500	34.9460
1.0000	42.8978
1.2500	48.7941
1.5000	52.9311
1.7500	55.7114
2.0000	57.5253
2.2500	58.6884
2.5000	59.4294
2.7500	59.9041
3.0000	60.2129
3.2500	60.4197
3.5000	60.5642
3.7500	60.6706
4.0000	60.7539

PARAMETER VG=-0.5V;

FORMAT VD(V) ID(mA);

0.0000	0.0035
0.2500	7.4314
0.5000	14.1644
0.7500	19.7929
1.0000	24.1821
1.2500	27.4269
1.5000	29.7468

1.7500	31.3866
2.0000	32.5575
2.2500	33.4197
2.5000	34.0837
2.7500	34.6235
3.0000	35.0866
3.2500	35.5024
3.5000	35.8897
3.7500	36.2601
4.0000	36.6207

PARAMETER VG=-1V;
 FORMAT VD(V) ID(mA);

0.0000	0.0036
0.2500	2.6750
0.5000	5.1785
0.7500	7.3260
1.0000	9.0548
1.2500	10.3993
1.5000	11.4392
1.7500	12.2595
2.0000	12.9317
2.2500	13.5088
2.5000	14.0269
2.7500	14.5105
3.0000	14.9757
3.2500	15.4319
3.5000	15.8855
3.7500	16.3407
4.0000	16.7994

PARAMETER VG=-1.5V;
 FORMAT VD(V) ID(mA);

0.0000	0.0037
0.2500	1.4568
0.5000	2.7520
0.7500	3.7922
1.0000	4.5584
1.2500	5.0871
1.5000	5.4354
1.7500	5.6577
2.0000	5.7967
2.2500	5.8826
2.5000	5.9352
2.7500	5.9681
3.0000	6.0098
3.2500	6.0742
3.5000	6.1637
3.7500	6.2797
4.0000	6.4226

PARAMETER VG=-2V;
 FORMAT VD(V) ID(mA);

0.0000	0.0038
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0.2500	1.4568
0.5000	2.7521
0.7500	3.7922
1.0000	4.5585
1.2500	5.0873
1.5000	5.4355
1.7500	5.6577
2.0000	5.7967
2.2500	5.8826
2.5000	5.9352
2.7500	5.9673
3.0000	5.9867
3.2500	5.9985
3.5000	6.0058
3.7500	6.0102
4.0000	6.0128

! Small-Signal S-Parameters

!

PARAMETER VG=0V VD=2V;

FORMAT	FREQ(GHZ)	MS11	PS11(DEG)	MS21	PS21(DEG)	MS12	PS12(DEG)	MS22	PS22(DEG);
	1.00	0.9940	-13.96	3.6413	168.72	0.0065	87.11	0.4501	-9.10
	3.00	0.9615	-41.14	3.4342	150.39	0.0186	83.94	0.4392	-16.81
	5.00	0.9111	-66.46	3.1320	133.11	0.0286	83.49	0.4364	-25.80
	7.00	0.8597	-89.44	2.7945	117.82	0.0376	86.24	0.4366	-34.45
	9.00	0.8172	-110.10	2.4711	104.47	0.0476	90.79	0.4407	-42.68
	11.00	0.7869	-128.63	2.1822	92.79	0.0605	95.04	0.4484	-50.58
	13.00	0.7682	-145.28	1.9317	82.52	0.0767	97.63	0.4593	-58.23
	15.00	0.7590	-160.24	1.7168	73.42	0.0962	98.30	0.4726	-65.68

! Small-Signal S-Parameters

!

PARAMETER VG=-0.5V VD=2V;

FORMAT	FREQ(GHZ)	MS11	PS11(DEG)	MS21	PS21(DEG)	MS12	PS12(DEG)	MS22	PS22(DEG);
	1.00	0.9960	-12.01	3.5763	169.54	0.0060	86.78	0.5472	-8.70
	3.00	0.9680	-35.60	3.4136	152.88	0.0170	82.98	0.5334	-16.11
	5.00	0.9220	-58.10	3.1744	136.68	0.0256	82.08	0.5273	-24.78
	7.00	0.8709	-79.16	2.8911	121.91	0.0326	85.43	0.5233	-33.09
	9.00	0.8247	-98.73	2.6031	108.67	0.0402	92.18	0.5228	-40.96
	11.00	0.7883	-116.86	2.3323	96.85	0.0512	99.27	0.5264	-48.49
	13.00	0.7630	-133.63	2.0876	86.27	0.0668	104.00	0.5337	-55.77
	15.00	0.7483	-149.10	1.8702	76.79	0.0866	105.75	0.5440	-62.91

! Small-Signal S-Parameters

!

PARAMETER VG=-1V VD=2V;

FORMAT	FREQ(GHZ)	MS11	PS11(DEG)	MS21	PS21(DEG)	MS12	PS12(DEG)	MS22	PS22(DEG);
	1.00	0.9975	-10.61	2.3881	170.26	0.0057	86.26	0.6381	-8.51
	3.00	0.9797	-31.65	2.3087	155.17	0.0159	81.69	0.6235	-15.72
	5.00	0.9488	-52.17	2.1945	139.99	0.0234	79.88	0.6175	-24.35
	7.00	0.9118	-71.96	2.0491	125.67	0.0284	83.36	0.6126	-32.79
	9.00	0.8752	-90.89	1.8886	112.44	0.0335	92.88	0.6101	-40.86
	11.00	0.8438	-108.90	1.7258	100.35	0.0427	104.40	0.6107	-48.58
	13.00	0.8198	-125.93	1.5685	89.38	0.0584	112.11	0.6146	-56.04
	15.00	0.8038	-141.95	1.4211	79.52	0.0801	114.72	0.6213	-63.31

! Small-Signal S-Parameters

!

PARAMETER VG=-1.5V VD=2V;

FORMAT	FREQ(GHZ)	MS11	PS11(DEG)	MS21	PS21(DEG)	MS12	PS12(DEG)	MS22	PS22(DEG);
	1.00	0.9997	-9.48	0.0055	85.26	0.0055	85.27	0.7798	-8.35
	3.00	0.9973	-28.44	0.0152	78.79	0.0152	78.79	0.7661	-15.23
	5.00	0.9927	-47.42	0.0216	74.42	0.0216	74.42	0.7654	-23.87
	7.00	0.9864	-66.37	0.0238	76.16	0.0238	76.16	0.7658	-32.69
	9.00	0.9789	-85.20	0.0241	90.68	0.0241	90.68	0.7665	-41.47
	11.00	0.9708	-103.71	0.0307	115.20	0.0307	115.20	0.7673	-50.11
	13.00	0.9624	-121.69	0.0492	128.97	0.0492	128.97	0.7677	-58.57
	15.00	0.9540	-138.87	0.0767	130.76	0.0767	130.76	0.7675	-66.81

! Small-Signal S-Parameters

!

PARAMETER VG=-2V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9997	-8.72	0.0052	85.52	0.0052	85.51	0.7798	-8.34
3.00	0.9977	-26.20	0.0145	79.59	0.0145	79.59	0.7661	-15.18
5.00	0.9937	-43.80	0.0208	75.53	0.0208	75.53	0.7654	-23.79
7.00	0.9881	-61.54	0.0231	77.05	0.0231	77.05	0.7657	-32.59
9.00	0.9812	-79.39	0.0233	90.59	0.0233	90.59	0.7665	-41.33
11.00	0.9734	-97.22	0.0290	115.34	0.0290	115.34	0.7672	-49.96
13.00	0.9651	-114.83	0.0463	130.66	0.0463	130.66	0.7677	-58.40
15.00	0.9564	-131.96	0.0732	133.30	0.0732	133.30	0.7675	-66.62

Data for Raytheon model

! DC Data (I-V Characteristics)

!

PARAMETER VG=0.5V;

FORMAT VD(V) ID(mA);

0.0000	-74.4389
0.2500	2.4488
0.5000	24.1092
0.7500	38.1360
1.0000	49.8242
1.2500	59.2855
1.5000	66.6622
1.7500	72.1443
2.0000	75.9748
2.2500	78.4518
2.5000	79.9286
2.7500	80.8089
3.0000	81.5121
3.2500	82.2121
3.5000	82.9120
3.7500	83.6111
4.0000	84.3099

PARAMETER VG=0V;

FORMAT VD(V) ID(mA);

0.0000	0.0000
0.2500	12.4408
0.5000	22.9887
0.7500	31.7500
1.0000	38.8412
1.2500	44.3957
1.5000	48.5672
1.7500	51.5335
2.0000	53.4998
2.2500	54.7005
2.5000	55.3987
2.7500	55.8807
3.0000	56.3439
3.2500	56.8068
3.5000	57.2692
3.7500	57.7310
4.0000	58.1924

PARAMETER VG=-0.5V;

FORMAT VD(V) ID(mA);

0.0000	0.0031
0.2500	7.5083
0.5000	13.7528
0.7500	18.8369
1.0000	22.8650
1.2500	25.9477
1.5000	28.2035
1.7500	29.7610

2.0000	30.7598
2.2500	31.3514
2.5000	31.6997
2.7500	31.9709
3.0000	32.2399
3.2500	32.5087
3.5000	32.7774
3.7500	33.0459
4.0000	33.3140

PARAMETER VG=-1V;

FORMAT VD(V) ID(mA);

0.0000	0.0033
0.2500	3.5176
0.5000	6.4011
0.7500	8.7144
1.0000	10.5185
1.2500	11.8754
1.5000	12.8493
1.7500	13.5070
2.0000	13.9187
2.2500	14.1584
2.5000	14.3033
2.7500	14.4268
3.0000	14.5502
3.2500	14.6735
3.5000	14.7966
3.7500	14.9199
4.0000	15.0428

PARAMETER VG=-1.5V;

FORMAT VD(V) ID(mA);

0.0000	0.0034
0.2500	0.9057
0.5000	1.6414
0.7500	2.2274
1.0000	2.6805
1.2500	3.0180
1.5000	3.2575
1.7500	3.4172
2.0000	3.5155
2.2500	3.5725
2.5000	3.6080
2.7500	3.6396
3.0000	3.6712
3.2500	3.7029
3.5000	3.7345
3.7500	3.7662
4.0000	3.7977

PARAMETER VG=-2V;

FORMAT VD(V) ID(mA);

0.0000	0.0035
0.2500	0.0036

0.5000	0.0037
0.7500	0.0038
1.0000	0.0038
1.2500	0.0039
1.5000	0.0039
1.7500	0.0040
2.0000	0.0041
2.2500	0.0041
2.5000	0.0042
2.7500	0.0041
3.0000	0.0041
3.2500	0.0043
3.5000	0.0041
3.7500	0.0041
4.0000	0.0043

! Small-Signal S-Parameters

!

PARAMETER VG=0V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9935	-14.39	3.5868	166.12	0.0071	86.69	0.4305	-9.49
3.00	0.9597	-42.12	3.3618	142.77	0.0200	82.85	0.4196	-17.73
5.00	0.9115	-67.35	3.0448	121.00	0.0307	81.70	0.4174	-27.02
7.00	0.8681	-89.63	2.7098	101.62	0.0399	83.71	0.4202	-35.78
9.00	0.8388	-109.21	2.4032	84.38	0.0497	87.77	0.4287	-44.07
11.00	0.8251	-126.54	2.1369	68.83	0.0618	92.17	0.4427	-52.06
13.00	0.8252	-142.04	1.9074	54.54	0.0772	95.52	0.4612	-59.88
15.00	0.8362	-156.10	1.7060	41.21	0.0963	97.21	0.4833	-67.61

! Small-Signal S-Parameters

!

PARAMETER VG=-0.5V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9961	-12.33	3.1466	166.88	0.0067	85.67	0.6016	-8.81
3.00	0.9694	-36.39	2.9920	145.23	0.0185	80.01	0.5853	-16.47
5.00	0.9286	-58.90	2.7720	124.37	0.0272	77.39	0.5776	-25.18
7.00	0.8884	-79.52	2.5231	105.26	0.0331	79.67	0.5738	-33.39
9.00	0.8584	-98.31	2.2799	87.86	0.0386	86.98	0.5762	-41.12
11.00	0.8421	-115.49	2.0564	71.90	0.0472	96.65	0.5851	-48.59
13.00	0.8393	-131.33	1.8542	57.07	0.0613	104.56	0.5999	-55.97
15.00	0.8482	-146.03	1.6693	43.12	0.0814	108.70	0.6192	-63.39

! Small-Signal S-Parameters

!

PARAMETER VG=-1V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9973	-10.91	2.3390	167.46	0.0063	84.99	0.7224	-8.58
3.00	0.9785	-32.39	2.2508	147.14	0.0175	78.15	0.7041	-15.96
5.00	0.9483	-52.99	2.1268	127.03	0.0251	73.98	0.6949	-24.56
7.00	0.9163	-72.44	1.9764	108.14	0.0289	75.39	0.6882	-32.80
9.00	0.8902	-90.73	1.8179	90.58	0.0312	85.02	0.6866	-40.61
11.00	0.8741	-107.93	1.6610	74.25	0.0371	100.88	0.6911	-48.12
13.00	0.8691	-124.16	1.5091	58.98	0.0510	113.79	0.7013	-55.53
15.00	0.8743	-139.51	1.3617	44.58	0.0731	119.35	0.7161	-62.97

! Small-Signal S-Parameters

!

PARAMETER VG=-1.5V VD=2V;

FORMAT FREQ(GHZ) MS11 PS11(DEG) MS21 PS21(DEG) MS12 PS12(DEG) MS22 PS22(DEG);

1.00	0.9985	-9.82	1.2561	167.94	0.0061	84.72	0.7923	-8.45
3.00	0.9881	-29.34	1.2235	148.68	0.0168	77.41	0.7748	-15.59
5.00	0.9704	-48.51	1.1803	129.22	0.0239	72.15	0.7682	-24.21
7.00	0.9500	-67.18	1.1224	110.56	0.0265	72.30	0.7629	-32.71
9.00	0.9316	-85.28	1.0532	92.97	0.0265	83.06	0.7603	-40.91
11.00	0.9183	-102.77	0.9755	76.50	0.0305	105.18	0.7615	-48.86
13.00	0.9114	-119.62	0.8908	61.17	0.0454	122.37	0.7665	-56.66
15.00	0.9108	-135.77	0.8004	46.96	0.0701	127.75	0.7743	-64.39

! Small-Signal S-Parameters

!

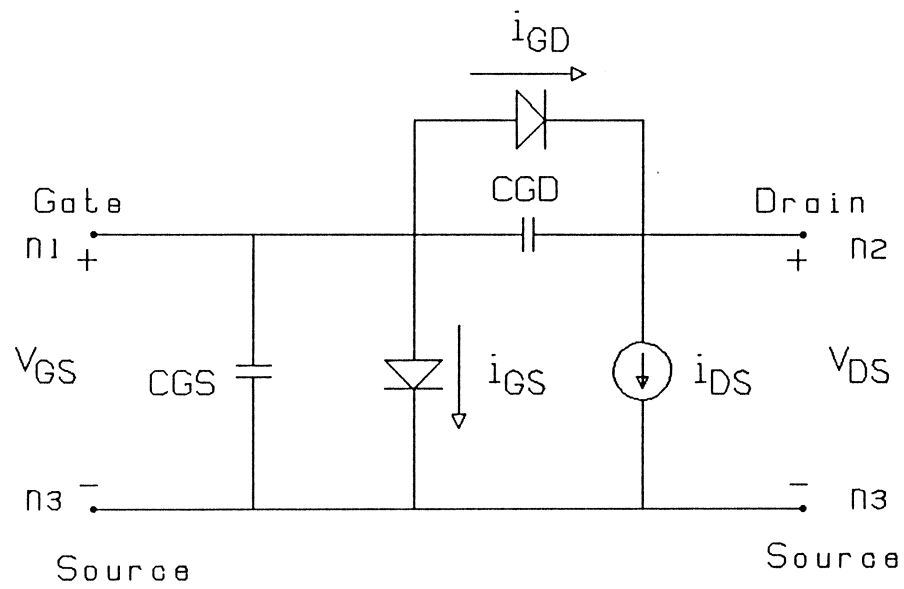
PARAMETER VG=-2V VD=2V;

FORMAT	FREQ(GHZ)	MS11	PS11(DEG)	MS21	PS21(DEG)	MS12	PS12(DEG)	MS22	PS22(DEG);
	1.00	0.9997	-8.95	0.0059	90.26	0.0058	84.84	0.8138	-8.36
	3.00	0.9975	-26.88	0.0162	79.55	0.0161	77.69	0.7993	-15.26
	5.00	0.9934	-44.91	0.0232	73.19	0.0230	72.04	0.7981	-23.92
	7.00	0.9876	-63.03	0.0255	72.05	0.0251	71.26	0.7978	-32.76
	9.00	0.9806	-81.18	0.0244	82.56	0.0239	82.29	0.7977	-41.55
	11.00	0.9729	-99.23	0.0275	108.84	0.0271	109.35	0.7975	-50.21
	13.00	0.9646	-116.97	0.0436	128.37	0.0434	128.89	0.7969	-58.69
	15.00	0.9562	-134.12	0.0705	132.58	0.0705	132.89	0.7955	-66.94

FETC

Curtice and Ettenberg FET model

FETC



FETC**Curtice and Ettenberg FET model****FETC****Keywords****Defaults**

A0	Cubic fit i_{DS} equation coefficient	0
A1	Cubic fit i_{DS} equation coefficient	0
A2	Cubic fit i_{DS} equation coefficient	0
A3	Cubic fit i_{DS} equation coefficient	0
GAMMA	Hyperbolic tangent function parameter	0
BETA	Coefficient for pinch-off change with respect to v_{DS}	0
VDS0	v_{DS} at which A0, A1, A2 and A3 were evaluated	0
TAU	Transit time under gate	0
IS	Gate junction saturation current (diode model)	1.0E-14
N	Gate-drain and gate-source emission coefficient (diode model)	1.0
CGD0	Zero-bias gate-drain junction capacitance (diode model)	0
CGS0	Zero-bias gate-source junction capacitance (diode model)	0
FC	Coefficient for forward bias used in capacitance equation (diode model)	0.5
GMIN	Linear conductance associated with the Schottky junctions	1.0E-12
VBI	Built-in gate potential	0.8
VBR	Gate junction reverse bias breakdown voltage or drain gate reverse bias breakdown voltage with $v_{DS}=0$	$+\infty$

Form

```

FETC  n1  n2  n3  [A0=x1] [A1=x2] [A2=x3] [A3=x4]
        [GAMMA=x5] [BETA=x6] [VDS0=x7] [TAU=x8]
        [IS=x9] [N=x10] [CGD0=x11] [CGS0=x12] [FC=x13]
        [GMIN=x14] [VBI=x15] [VBR=x16];

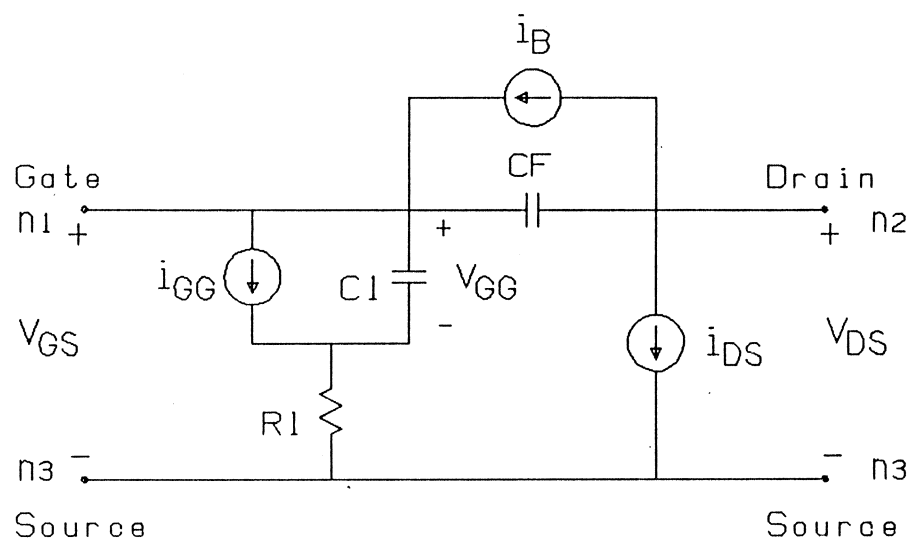
```

Example

```

FETC  2  4  3  A0=.065  A1=.115  A2=.059  GAMMA=2  VDS0=2  IS=3.7NA;

```

FETM**Materka and Kacprzak FET model****FETM**

FETM**Materka and Kacprzak FET model****FETM****Keywords****Defaults**

IDSS	Drain saturation current for $v_{GG}=0$	6.0E-2
VP0	Pinch-off voltage for $v_{DS}=0$	-2.0
GAMMA	Voltage-slope parameter of pinch-off voltage	0
E	Constant part of the exponent defining the dependence of saturation drain current on gate voltage	2.0
KE	Parameter describing the dependence of the exponent on gate voltage	0
SL	Slope of the $v_{GG}=0$ drain characteristic in the linear region	6.0E-2
KG	Parameter defining the dependence on gate voltage of the drain characteristics slope in the linear region	0
TAU	Channel transit-time delay	0
SS	Slope of the $v_{GG}=0$ drain characteristic in the saturation region	0
IG0	Saturation current of gate Schottky barrier	0
ALPHAG	Slope factor of gate conduction current	38.696
IB0	Channel breakdown current for $v_{DS}-v_{GS}=VBC$	0
ALPHAB	Slope factor of breakdown current	0
VBC	Channel breakdown voltage	$+\infty$
R10	Intrinsic channel resistance for zero gate voltage	3.5
KR	Voltage slope factor of intrinsic channel resistance	0
C10	Gate Schottky-barrier capacitance for $v_{GG}=0$	4.0E-4
K1	Voltage-slope parameter of gate capacitance	1.25
C1S	Parasitic additional constant component of the gate capacitance	0
CF0	Feedback capacitance for $v_{DS}=v_{GS}$	2.0E-5
KF	Voltage-slope parameter of feedback capacitance	0

Form

```

FETM n1 n2 n3 [IDSS=x1] [VP0=x2] [GAMMA=x3] [E=x4] [KE=x5]
        [SL=x6] [KG=x7] [TAU=x8] [SS=x9] [IG0=x10] [ALPHAG=x11]
        [IB0=x12] [ALPHAB=x13] [VBC=x14] [R10=x15] [KR=x16]
        [C10=x17] [K1=x18] [C1S=x19] [CF0=x20] [KF=x21];

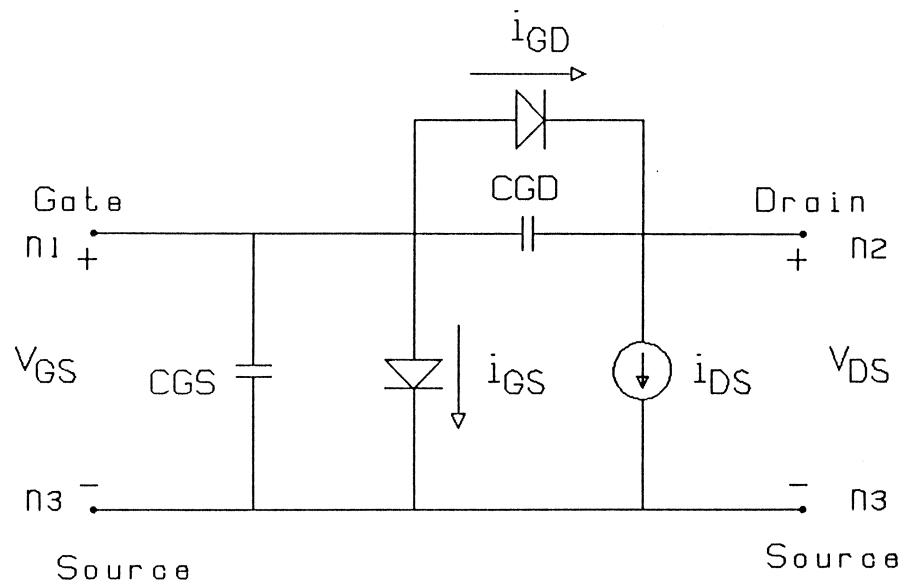
```

Example

```

FETM 2 4 3 IDSS=6.E-2 VP0=-1.9 SL=.0676 R10=3.5
        C10=.42PF K1=1.282 CF0=.02PF;

```

FETR**Raytheon FET model****FETR**

FETR**Raytheon FET model****FETR****Keywords****Defaults**

ALPHA	Hyperbolic tangent function parameter	0
BETA	Transconductance parameter	0
LAMBDA	Channel length modulation parameter	0
THETA	Transconductance parameter for large v_{GS}	0
VT0	Threshold voltage	-2.0
TAU	Transit time under gate	0
IS	Gate junction saturation current (diode model)	1.0E-14
N	Gate-drain and gate-source emission coefficient (diode model)	1.0
CGD0	Zero bias gate-drain junction capacitance (diode model)	0
CGS0	Zero bias gate-source junction capacitance (diode model)	0
FC	Coefficient for forward bias used in the capacitance equation (diode model)	0.5
GMIN	Linear conductance associated with the Schottky junctions	1.0E-12
VBI	Built-in gate potential	0.8
VBR	Gate junction reverse bias breakdown voltage or drain gate reverse bias breakdown voltage with $v_{DS}=0$	$+\infty$

Form

```
FETR n1 n2 n3 [ALPHA=x1] [BETA=x2] [LAMBDA=x3]
      [THETA=x4] [VT0=x5] [TAU=x6] [IS=x7]
      [N=x8] [CGS0=x9] [CGD0=x10] [FC=x11]
      [GMIN=x12] [VBI=x13] [VBR=x14];
```

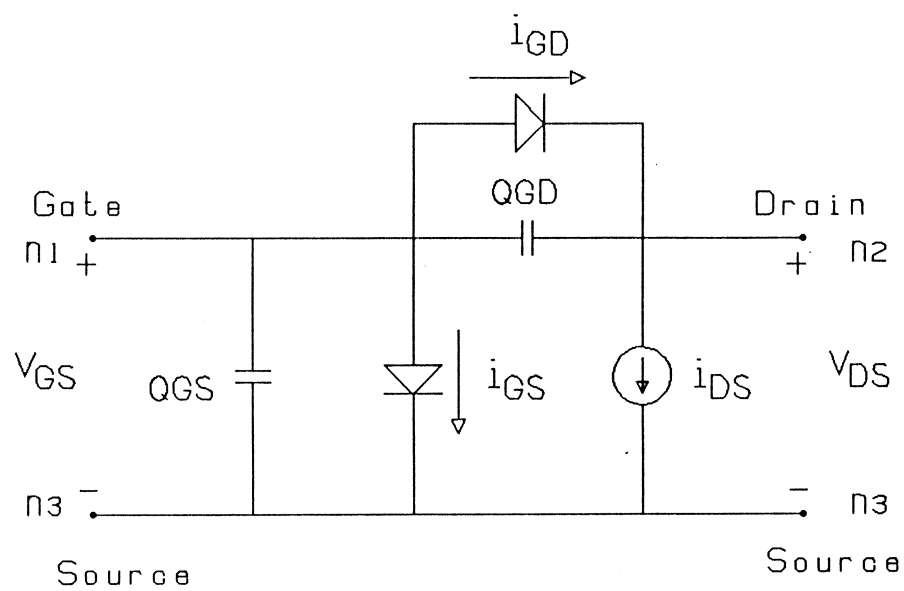
Example

```
FETR 2 4 3 BETA=0.02 VT0=-1.2 IS=3.7NA;
```

FETU1

User-definable FET model 1

FETU1



FETU1**User-definable FET model 1****FETU1****Keywords****Defaults**

TAU	Transit time under gate	0
IGS	Gate-source current	0
IDS	Drain-source current	0
IGD	Gate-drain current	0
QGS	Gate-source capacitor charge	0
QGD	Gate-drain capacitor charge	0

Form

FETU1 [TAU=x1] [IGS=x2] [IDS=x3] [IGD=x4] [QGS=x5] [QGD=x6];

Example

```
FETU1 TAU=3PS IGS=Igs_user IDS=Ids_user IGD=Igd_user
      QGS=Qgs_user QGD=Qgd_user;
```

where Igs_user, Ids_user, Igd_user, Qgs_user and Qgd_user are labels which are user-defined in the EXPR block.

The Model

The internal variables available are fundamental frequency FFREQ, bias voltages VG, VD, instantaneous voltages VGS_T, VDS_T and delayed instantaneous voltage VGS_TAU.

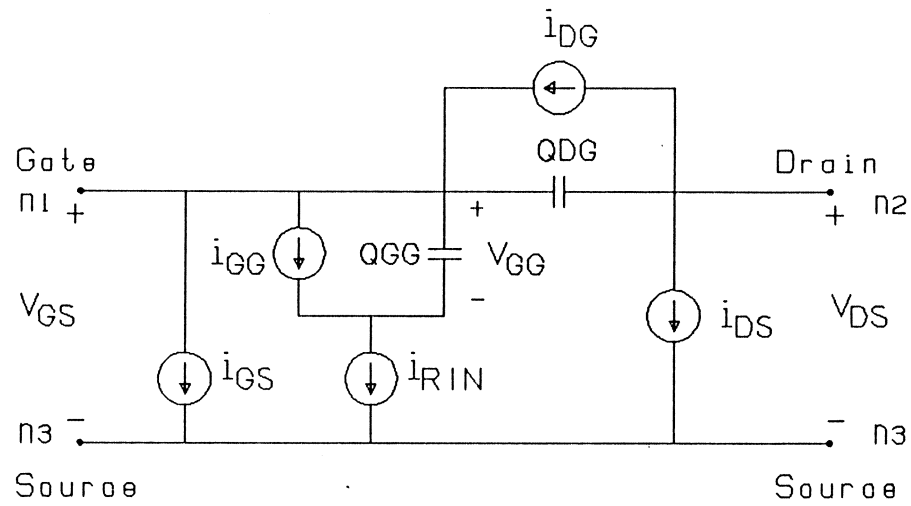
IGS, IGD, QGS and QGD can be functions of FFREQ, VG, VD, VGS_T and VDS_T.

IDS can be a function of FFREQ, VG, VD, VGS_T, VDS_T and VGS_TAU.

FETU2

User-definable FET model 2

FETU2



FETU2**User-definable FET model 2****FETU2****Keywords****Defaults**

TAU	Transit time under gate	0
IGS	Gate-source current	0
IDS	Drain-source current	0
IDG	Drain-gate current	0
IGG	Gate current	0
IRIN	Component of source current	0
QGG	Gate capacitor charge	0
QDG	Drain-gate capacitor charge	0

Form

```
FETU1 [TAU=x1] [IGS=x2] [IDS=x3] [IDG=x4] [IGG=x5]
      [IRIN=x6] [QGG=x7] [QDG=x8];
```

Example

```
FETU1 TAU=3PS IGS=Igs_user IDS=Ids_user IDG=Idg_user
      IGG=Igg_user IRIN=Irin_user QGG=Qgg_user QDG=Qdg_user;
```

where Igs_user, Ids_user, Idg_user, Igg_user, Irin_user, Qgg_user and Qdg_user are labels which are user-defined in the EXPR block.

The Model

The internal variables available are fundamental frequency FFREQ, bias voltages VG, VD, instantaneous voltages VGS_T, VDS_T, VGG_T and delayed instantaneous voltage VGS_TAU.

IGS, IDG, IGG, IRIN, QGG and QDG can be functions of FFREQ, VG, VD, VGS_T, VDS_T and VGG_T.

IDS can be a function of FFREQ, VG, VD, VGS_T, VDS_T, VGG_T and VGS_TAU.